

TOSHIBA Thyristor Silicon Planar Type

S6992

Condenser Discharge Control Applications

- Critical rate of rise of ON-state current: $di/dt = 750 \text{ A}/\mu\text{s}$
- Repetitive surge ON-state current: $I_{TRM} = 500 \text{ A}$ ($t_w = 2 \mu\text{s}$)
- Repetitive peak OFF-state voltage: $V_{DRM} = 800 \text{ V}$
- Gate trigger current: $I_{GT} = 20 \text{ mA max.}$

Absolute Maximum Ratings

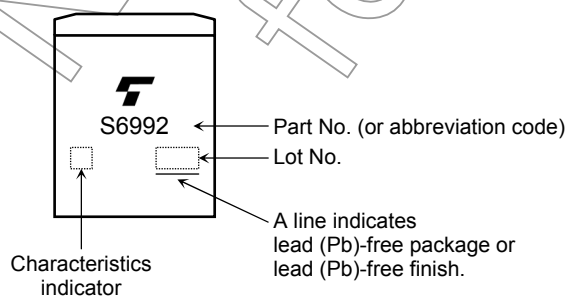
| Characteristics | Symbol | Rating | Unit |
|---|------------|---------|------------------------|
| Repetitive peak OFF-state voltage | V_{DRM} | 800 | V |
| Repetitive peak surge ON-state current (Note 1) | I_{TRM} | 500 | A |
| Critical rate of rise of ON-state current (Note 1) | di/dt | 750 | $\text{A}/\mu\text{s}$ |
| Peak gate power dissipation | P_{GM} | 5 | W |
| Average gate power dissipation | $P_G (AV)$ | 0.5 | W |
| Peak forward gate voltage | V_{FGM} | 10 | V |
| Peak reverse gate voltage | V_{RGM} | -5 | V |
| Peak forward gate current | I_{GM} | 2 | A |
| Junction temperature | T_j | -40~125 | $^{\circ}\text{C}$ |
| Storage temperature range | T_{stg} | -40~150 | $^{\circ}\text{C}$ |

Note 1: $V_D \leq 0.8 \times \text{rated}$, $T_c = 85^{\circ}\text{C}$, $i_{gp} \geq 40 \text{ mA}$, $t_{gw} \geq 10 \mu\text{s}$, $t_{gr} \geq 150 \text{ ns}$

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

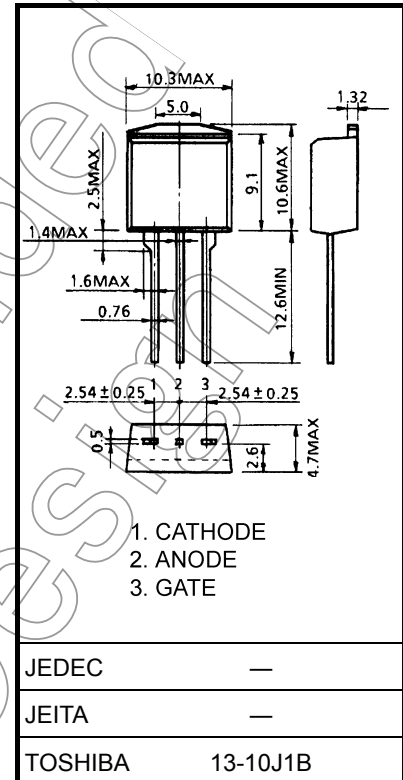
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Marking



*: There is no reverse-blocking (reverse voltage) ability.

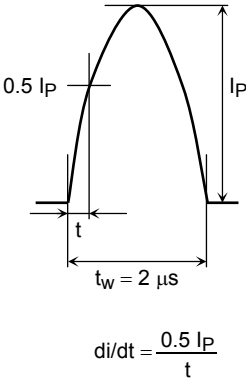
Unit: mm



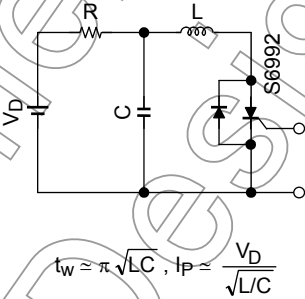
Weight: 1.5 g (typ.)

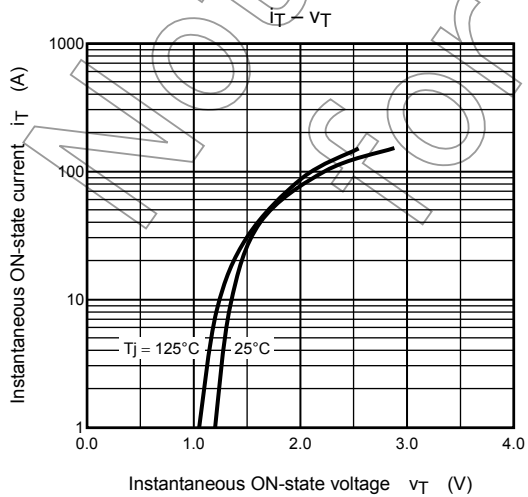
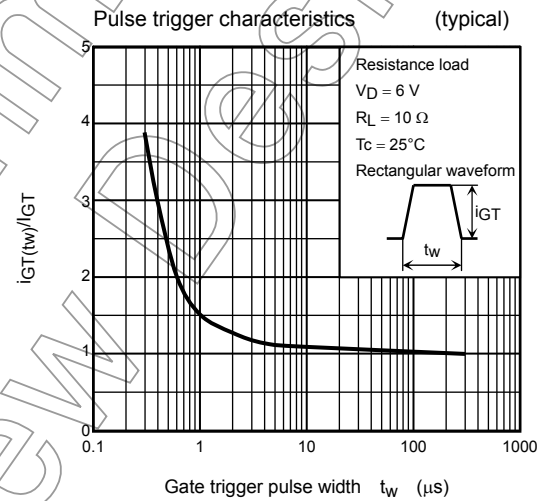
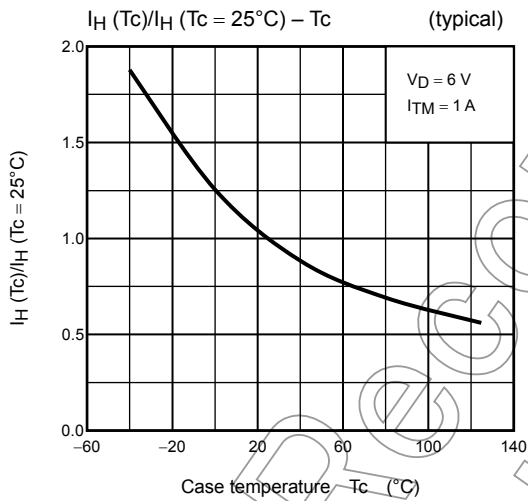
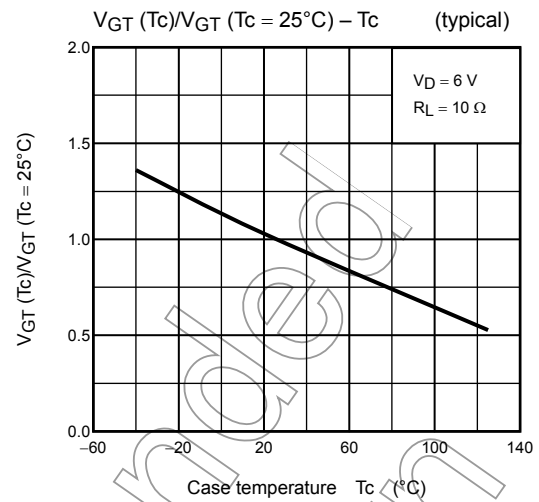
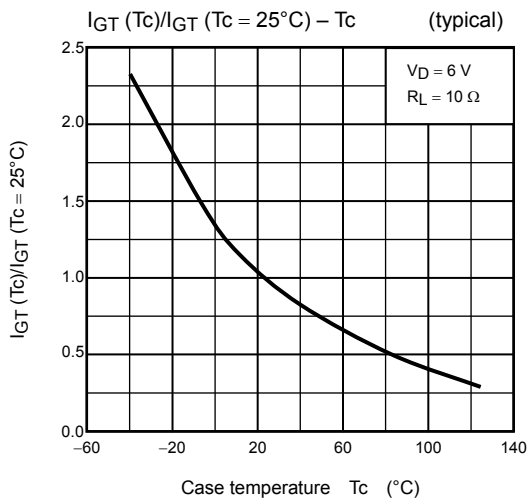
Electrical Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--|-----------------------|---|-----|------|-----|-----------------------------|
| Repetitive peak OFF-state current | I_{DRM} | $V_{\text{DRM}} = \text{rated}$ | — | — | 10 | μA |
| Peak ON-state voltage | V_{TM} | $I_{\text{TM}} = 25 \text{ A}$ | — | — | 1.5 | V |
| Gate trigger voltage | V_{GT} | $V_{\text{D}} = 6 \text{ V}, R_{\text{L}} = 10 \Omega$ | — | — | 1.0 | V |
| Gate trigger current | I_{GT} | | — | — | 20 | mA |
| Gate non-trigger voltage | V_{GD} | $V_{\text{D}} = \text{rated}, T_{\text{c}} = 125^{\circ}\text{C}$ | 0.2 | — | — | V |
| Critical rate of rise of OFF-state voltage | dv/dt | $V_{\text{DRM}} = \text{rated}, T_{\text{c}} = 125^{\circ}\text{C}$ Exponential rise | — | 50 | — | $\text{V}/\mu\text{s}$ |
| Holding current | I_{H} | $V_{\text{D}} = 6 \text{ V}, I_{\text{TM}} = 1 \text{ A}$ | — | — | 40 | mA |
| Thermal resistance | $R_{\text{th (j-a)}}$ | Junction to ambient | — | — | 70 | $^{\circ}\text{C}/\text{W}$ |



Test Circuit Examples





RESTRICTIONS ON PRODUCT USE

20070701-EN

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